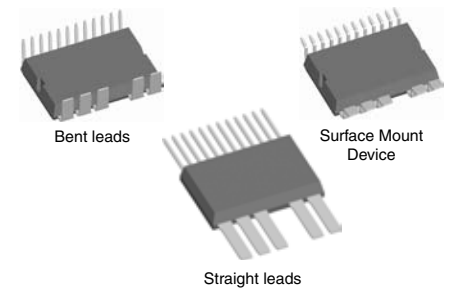
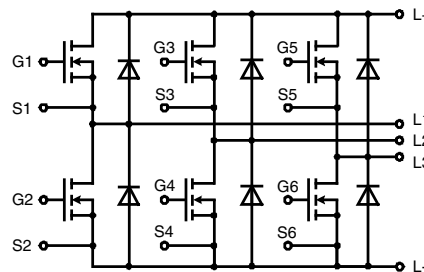


Three phase full Bridge with Trench MOSFETs in DCB isolated high current package

$$\begin{aligned}
V_{DSS} &= 75 \text{ V} \\
I_{D25} &= 118 \text{ A} \\
R_{DSon \text{ typ.}} &= 3.7 \text{ m}\Omega
\end{aligned}$$



MOSFETs			
Symbol	Conditions	Maximum Ratings	
V_{DSS}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	75	V
V_{GS}		± 20	V
I_{D25}	$T_C = 25^{\circ}\text{C}$	118	A
I_{D90}	$T_C = 90^{\circ}\text{C}$	85	A
I_{F25}	$T_C = 25^{\circ}\text{C (diode)}$	120	A
I_{F90}	$T_C = 90^{\circ}\text{C (diode)}$	78	A

Applications

AC drives

- in automobiles
 - electric power steering
 - starter generator
- in industrial vehicles
 - propulsion drives
 - fork lift drives
- in battery supplied equipment

Features

- MOSFETs in trench technology:
 - low R_{DSon}
 - optimized intrinsic reverse diode
- package:
 - high level of integration
 - high current capability 300 A max.
 - aux. terminals for MOSFET control
 - terminals for soldering or welding connections
 - isolated DCB ceramic base plate with optimized heat transfer
- Space and weight savings

Package options

- 3 lead forms available
 - straight leads (SL)
 - SMD lead version (SMD)
 - bent leads (BL)

Symbol	Conditions	Characteristic Values			
		(T _{VJ} = 25°C, unless otherwise specified)			
		min.	typ.	max.	
R_{DSon}	on chip level at $V_{GS} = 10 \text{ V}; I_D = 60 \text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		3.7 8.4	5.5 mΩ
$V_{GS(th)}$	$V_{DS} = 20 \text{ V}; I_D = 1 \text{ mA}$			2	4 V
I_{DSS}	$V_{DS} = V_{DSS}; V_{GS} = 0 \text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		0.1	1 μA
I_{GSS}	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$			0.2	μA
Q_g Q_{gs} Q_{gd}	$V_{GS} = 10 \text{ V}; V_{DS} = 55 \text{ V}; I_D = 125 \text{ A}$		100 19 28		nC nC nC
$t_{d(on)}$ t_r $t_{d(off)}$ t_f			80 80 510 100		ns ns ns ns
E_{on} E_{off} E_{recoff}			0.12 0.40 0.02		mJ mJ mJ
R_{thJC} R_{thJH}	with heat transfer paste (IXYS test setup)		1.3	1.0 1.6	K/W K/W

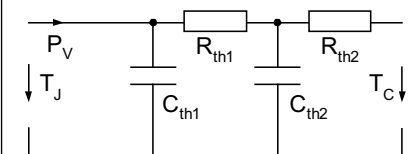
Source-Drain Diode

Symbol	Conditions	Characteristic Values			
		(T _J = 25°C, unless otherwise specified)			
		min.	typ.	max.	
V _{SD}	(diode) I _F = 60 A; V _{GS} = 0 V		0.9	1.2	V
t _{rr}	I _F = 80 A; -di _F /dt = 800 A/μs; V _R = 30 V		70		ns
Q _{RM}			1.1		μC
I _{RM}			30		A

Component

Symbol	Conditions	Maximum Ratings	
I _{RMS}	per pin in main current paths (P+, N-, L1, L2, L3) may be additionally limited by external connections	300	A
T _{VJ}		-55...+175	°C
T _{stg}		-55...+125	°C
V _{ISOL}	I _{ISOL} ≤ 1 mA, 50/60 Hz, f = 1 minute	1000	V~
F _C	mounting force with clip	50 - 250	N

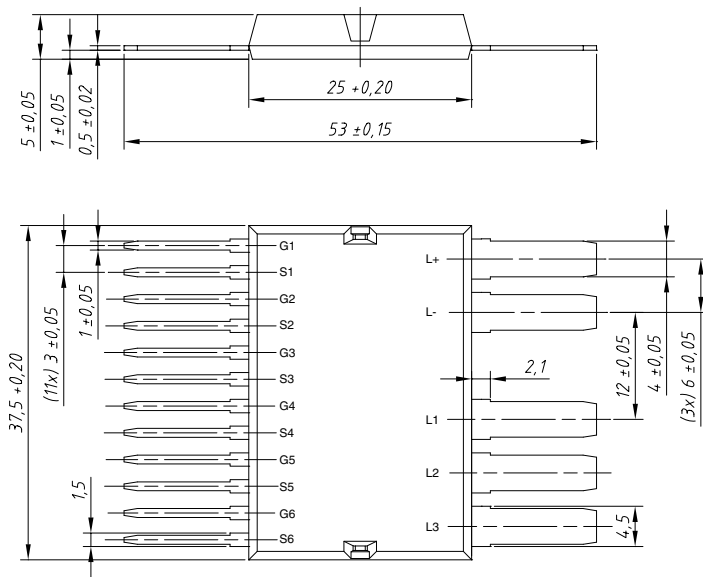
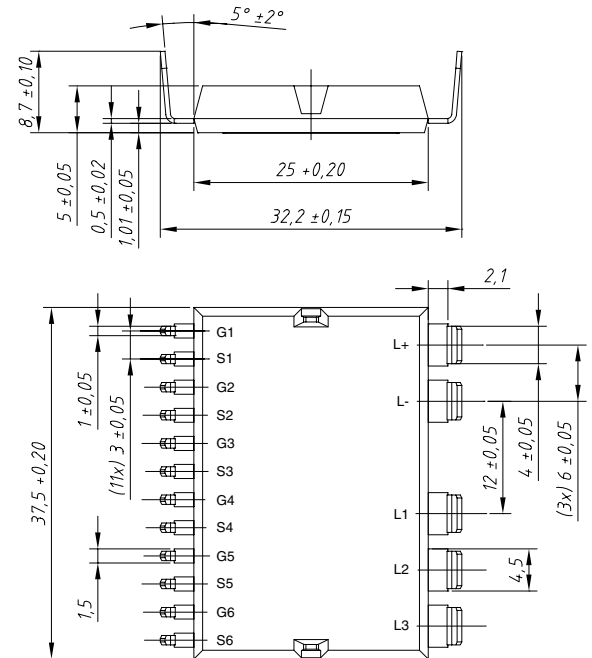
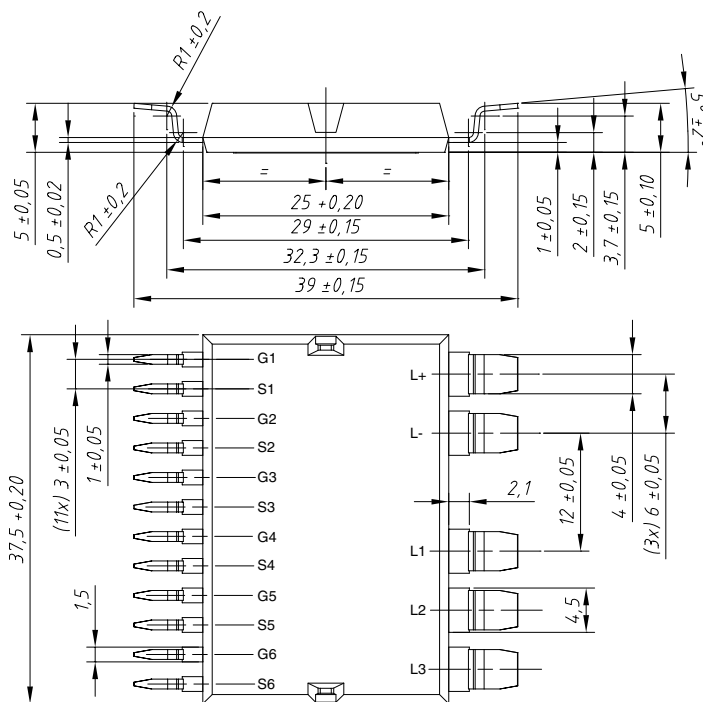
Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
R _{pin to chip}	with heatsink compound		0.6		mΩ
C _p	coupling capacity between shorted pins and mounting tab in the case		160		pF
Weight	typ.		25		g

Equivalent Circuits for Simulation
Thermal Response


junction - case (typ.)

$$C_{th1} = 0.039 \text{ J/K}; R_{th1} = 0.28 \text{ K/W}$$

$$C_{th2} = 0.069 \text{ J/K}; R_{th2} = 0.57 \text{ K/W}$$

Straight Leads GWM 120-0075P3-SL

Bent Leads GWM 120-0075P3-BL

Surface Mount Device GWM 120-0075P3-SMD


Leads	Ordering	Part Name & Packing Unit Marking	Part Marking	Delivering Mode	Base Qty.	Ordering Code
Straight	Standard	GWM 120-0075P3 - SL	GWM 120-0075P3	Blister	36	502 843
SMD	Standard	GWM 120-0075P3 - SMD	GWM 120-0075P3	Blister	36	502 850
Bent	Standard	GWM 120-0075P3 - BL	GWM 120-0075P3	Blister	36	contact factory

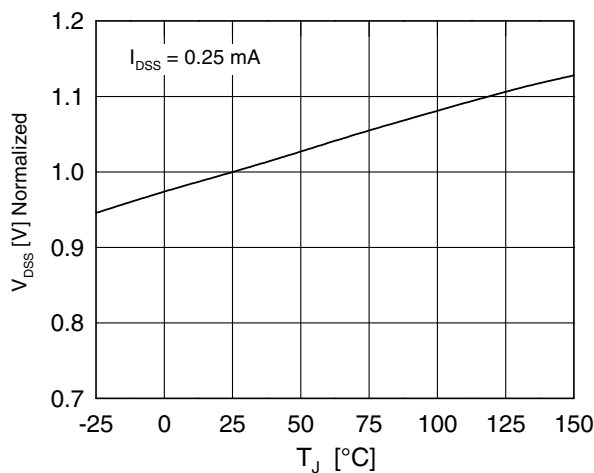


Fig. 1 Drain source breakdown voltage V_{DS} vs. junction temperature T_J

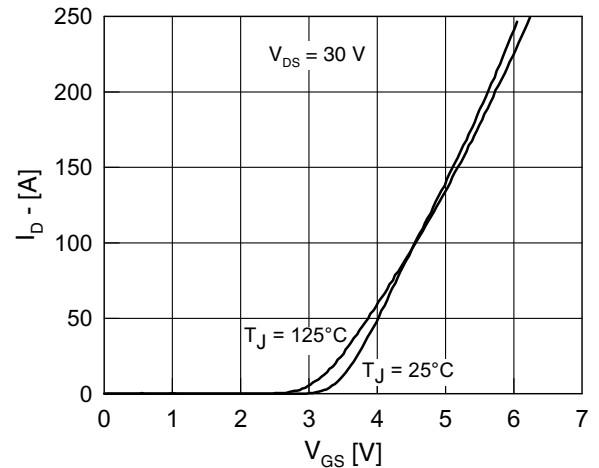


Fig. 2 Typical transfer characteristic

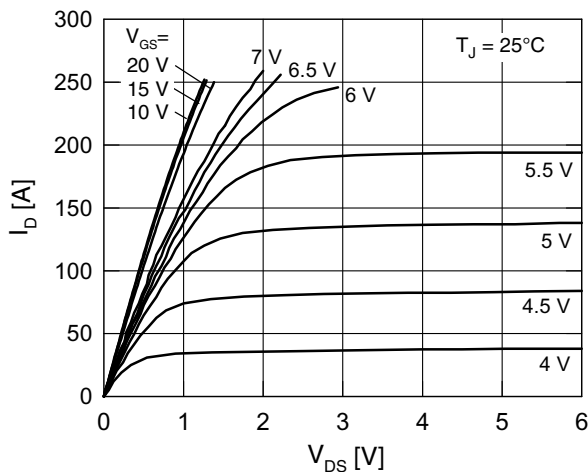


Fig. 3 Typical output characteristic

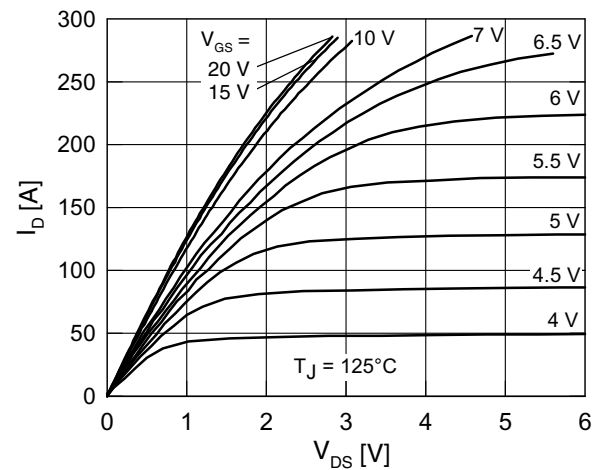


Fig. 4 Typical output characteristic

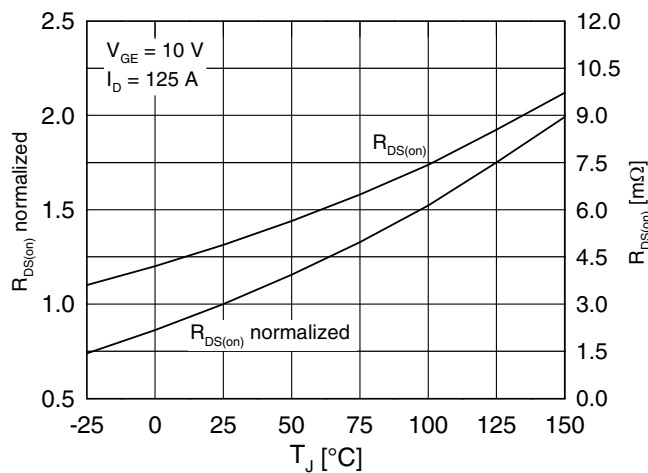


Fig. 5 Drain source on-state resistance $R_{DS(on)}$ versus junction temperature T_J

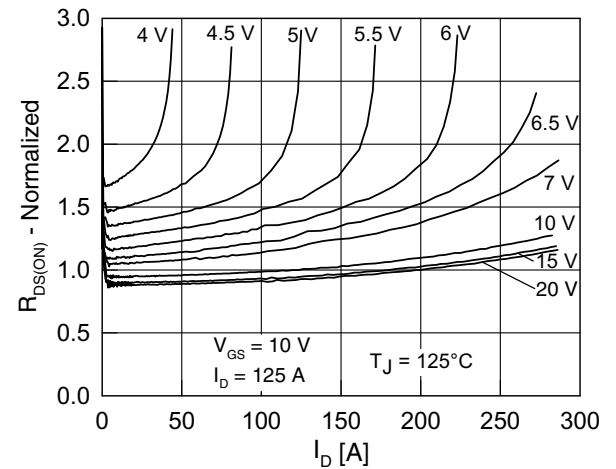


Fig. 6 Drain source on-state resistance $R_{DS(on)}$ versus I_D

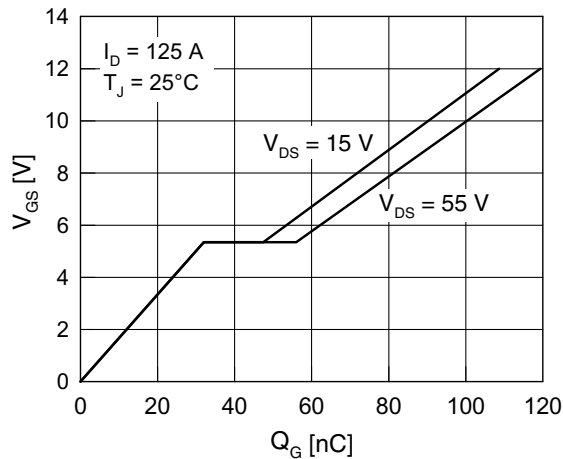


Fig. 7 Gate charge characteristic

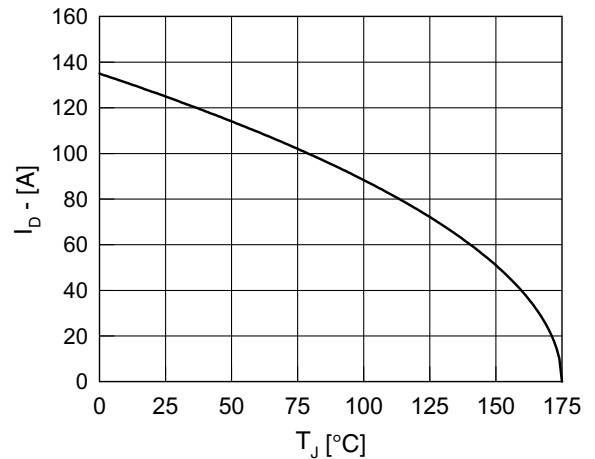


Fig. 8 Drain current I_D vs. case temperature T_J

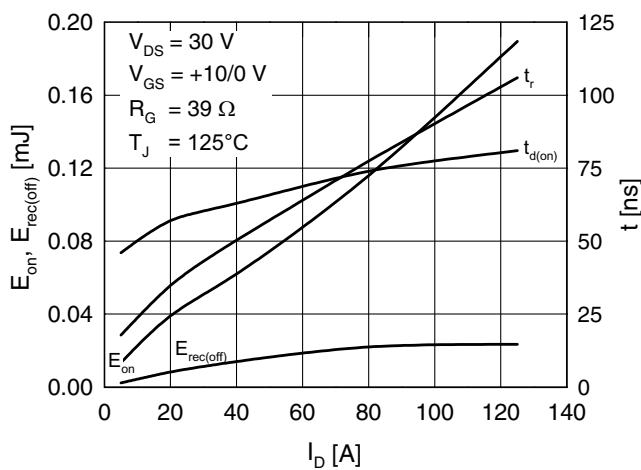


Fig. 9 Typ. turn-on energy & switching times vs. collector current, inductive switching

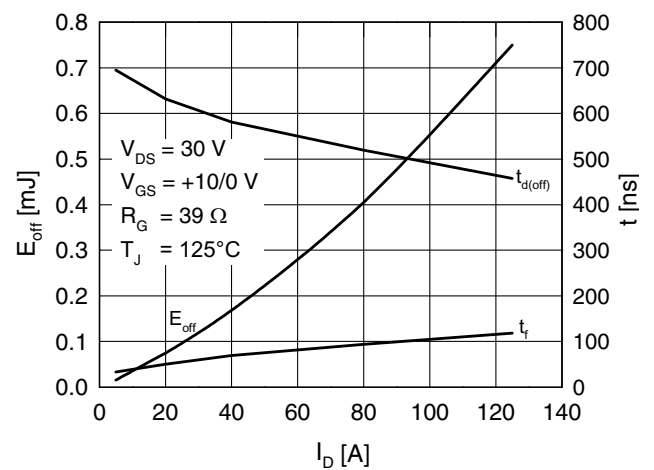


Fig. 10 Typ. turn-off energy & switching times vs. collector current, inductive switching

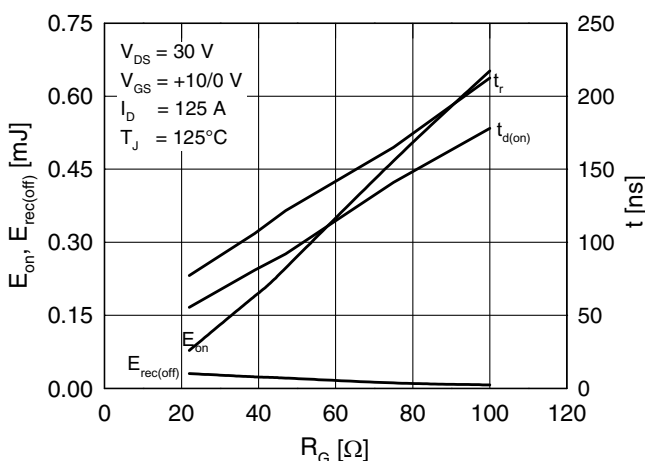


Fig. 11 Typ. turn-on energy & switching times vs. gate resistor, inductive switching

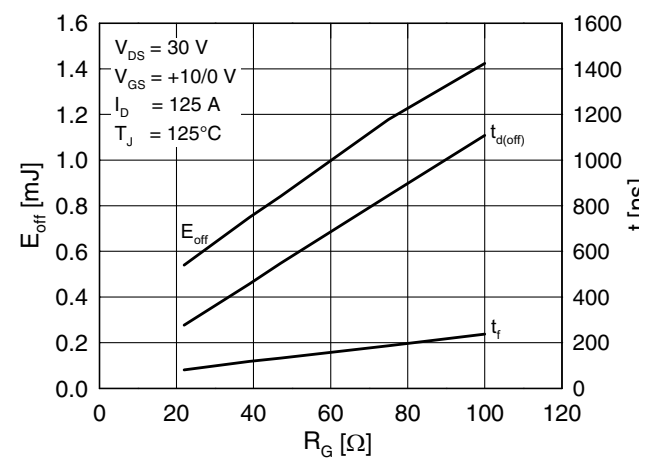


Fig. 12 Typ. turn-off energy & switching times vs. gate resistor, inductive switching

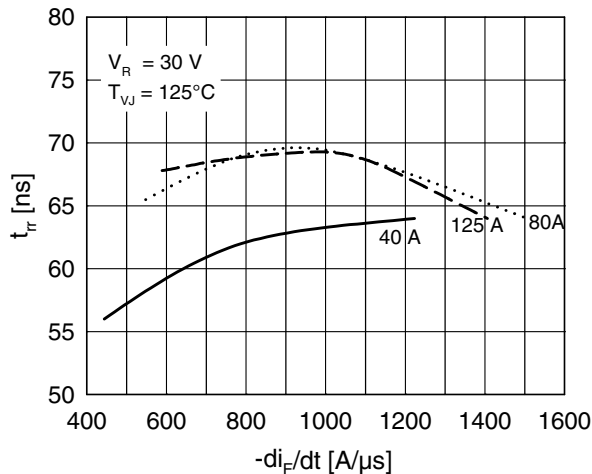


Fig. 13 Reverse recovery time t_{rr} of the body diode vs. di/dt

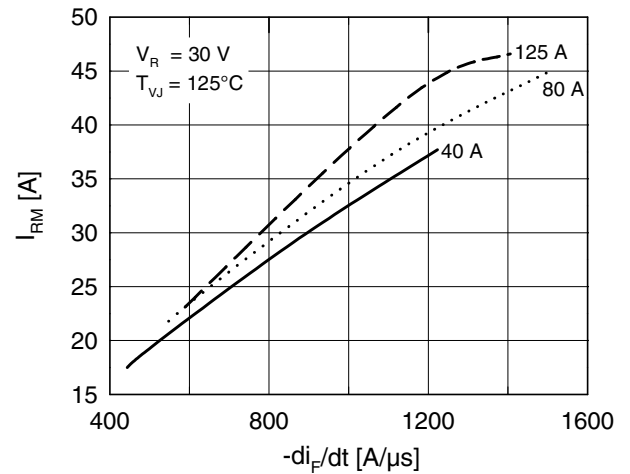


Fig. 14 Reverse recovery current I_{RM} of the body diode vs. di/dt

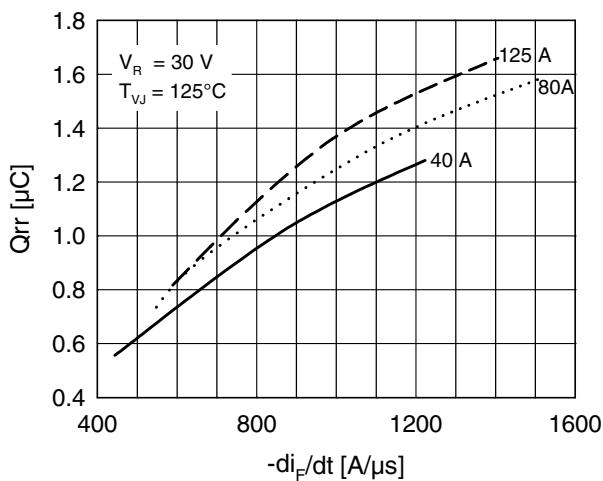


Fig. 15 Reverse recovery charge Q_{rr} of the body diode vs. di/dt

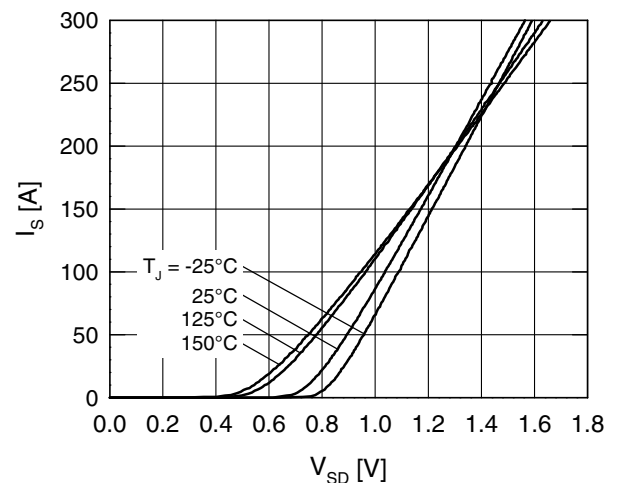


Fig. 16 Source current I_S vs. source drain voltage V_{SD} (body diode)

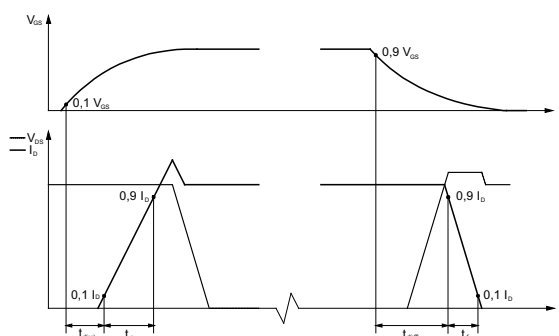


Fig. 17 Definition of switching times

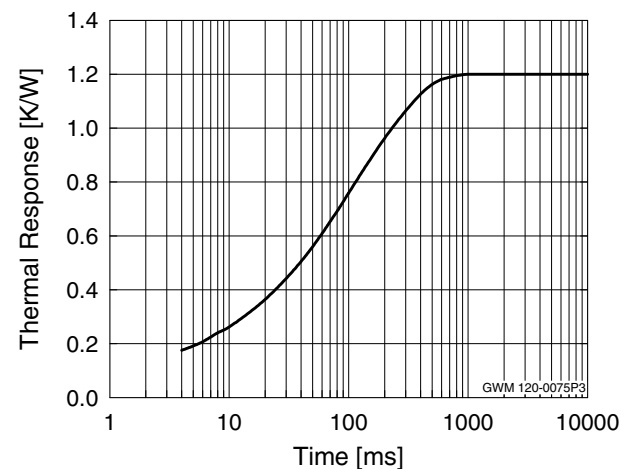


Fig. 18 Typ. therm. impedance junction to heatsink Z_{thJC}